

R2005240P12

GaAs Reverse Hybrid 5MHz to 200MHz

The R2005240P12 is a hybrid reverse amplifier. The part employs a GaAs die. It has extremely low distortion and superior return loss performance. The part also provides optimal reliability with low noise and is well suited for 5MHz to 200MHz CATV amplifiers for reverse channel systems.



Ordering Information

R2005240P12 Box with 50 pieces

Absolute Maximum Ratings

Parameter	Rating	Unit
RF Input Voltage (single tone)	70	dBmV
DC Supply Over-Voltage (5 minutes)	15	V
Storage Temperature	-40 to +100	°C
Operating Mounting Base Temperature	-30 to +100	°C



Package: SOT-115J

Features

- Excellent Linearity
- Superior Return Loss Performance
- Extremely Low Distortion
- Optimal Reliability
- Low Noise
- Unconditionally Stable Under All Terminations
- 24.2dB Typ. Gain at 200MHz
- 360mA Max. at 12VDC

Applications

 5MHz to 200MHz CATV Amplifier For Reverse Channel Systems



RoHS

Caution! ESD sensitive device.

RoHS (Restriction of Hazardous Substances): Compliant per EU Directive 2011/65/EU.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implie

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Nominal Operating Parameters

Parameter	Specification		11	Orandition		
Parameter	Min	Тур	Max	Unit x	Condition	
General Performance					V+ = 12V; T_{MB} = 30°C; Z_{S} = Z_{L} = 75 Ω	
Power Gain	23.5	24.2	24.5	dB	f = 5MHz	
	23.5	24.2	25.0	dB	f = 200MHz	
Slope ^[1]	-0.5	0.0	0.5	dB		
Flatness of Frequency Response			±0.5	dB	f = 5MHz to 200MHz	
Input Return Loss	20.0			dB		
Output Return Loss	20.0			dB		
Noise Figure		3.8	5.0	dB	f = 10MHz	
		1.8	2.3	dB	f = 200MHz	
Total Current Consumption (DC)	350.0	355.0	360.0	mA		
Distortion Data 5MHz to 200MHz					V+ = 12V; T _{MB} = 30°C; Z _S = Z _L = 75Ω	
СТВ			-70	dBc		
XMOD			-65	dB	26 ch flat; $V_0 = 50 dBm V^{[2]}$	
CSO			-70	dBc		
d ₂			-75	dBc	[3]	
Vo	65			dBmV	$D_{IM} = -60 dB^{[4]}$	

1. The slope is defined as the difference between the gain at the start frequency and the gain at the stop frequency.

2. 26 channels, NTSC frequency raster: T7 - T13 (7.0MHz to 43.0MHz), 2 - 6 (55.25MHz - 83.25MHz), A - 11 (121.25MHz - 199.25MHz), +50dBmV flat output level.

3. $f_1 = 83.25 MHz$; $V_1 = 50 dBmV$; $f_2 = 109.25 MHz$; $V_2 = 50 dBmV$; $f_{TEST} = f_1 + f_2 = 192.5 MHz$.

4. $f_1 = 187.25$ MHz; $V_1 = V_0$; $f_2 = 194.25$ MHz; $V_2 = V_1 - 6$ dB; $f_3 = 196.25$ MHz; $V_3 = V_1 - 6$ dB; $f_{TEST} = f_1 + f_2 - f_3 = 185.25$ MHz according to DIN45004B. Composite Second Order (CSO) - The CSO parameter (both sum and difference products) is defined by the NCTA.

Composite Triple Beat (CTB) - The CTB parameter is defined by the NCTA.

Cross Modulation (XMOD) - Cross modulation (XMOD) is measured at baseband (selective voltmeter method), referenced to 100% modulation of the carrier being tested.



Package Drawing (Dimensions in millimeters)



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